

2SB1079

Silicon PNP Triple Diffused

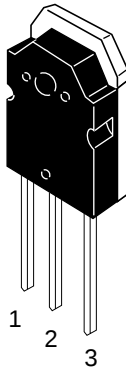
HITACHI

Application

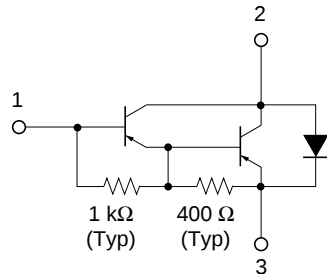
Low frequency power amplifier complementary pair with 2SD1559

Outline

TO-3P



- 1. Base
- 2. Collector (Flange)
- 3. Emitter



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	-100	V
Collector to emitter voltage	V_{CEO}	-100	V
Emitter to base voltage	V_{EBO}	-7	V
Collector current	I_C	-20	A
Collector peak current	$I_{C(peak)}$	-30	A
Base current	I_B	-3	A
Collector power dissipation	P_C^{*1}	100	W
Junction temperature	T_j	150	°C
Storage temperature	Tstg	-55 to +150	°C

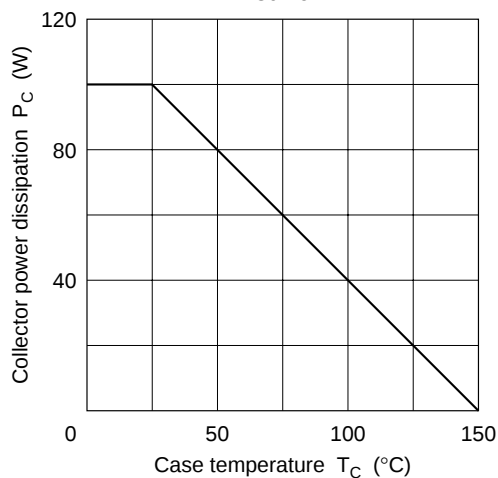
Note: 1. Value at $T_C = 25^\circ\text{C}$.

Electrical Characteristics (Ta = 25°C)

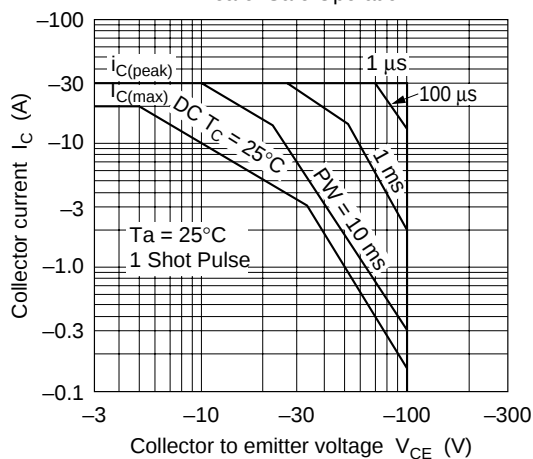
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-100	—	—	V	$I_C = -0.1\text{ mA}$, $I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-100	—	—	V	$I_C = -25\text{ mA}$, $R_{BE} = \infty$
Collector to emitter sustain voltage	$V_{CEO(sus)}$	-100	—	—	V	$I_C = -200\text{ mA}$, $R_{BE} = \infty^{*1}$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-7	—	—	V	$I_E = -50\text{ mA}$, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-100	μA	$V_{CB} = -100\text{ V}$, $I_E = 0$
	I_{CEO}	—	—	-1.0	mA	$V_{CE} = -80\text{ V}$, $R_{BE} = \infty$
DC current transfer ratio	h_{FE}	1000	—	20000		$V_{CE} = -3\text{ V}$, $I_C = -10\text{ A}^{*1}$
Collector to emitter saturation voltage	$V_{CE(sat)1}$	—	—	-2.0	V	$I_C = -10\text{ A}$, $I_B = -20\text{ mA}^{*1}$
Base to emitter saturation voltage	$V_{BE(sat)1}$	—	—	-2.5	V	
Collector to emitter saturation voltage	$V_{CE(sat)2}$	—	—	-3.0	V	$I_C = -20\text{ A}$, $I_B = -200\text{ mA}^{*1}$
Base to emitter saturation voltage	$V_{BE(sat)2}$	—	—	-3.5	V	
Turn on time	t_{on}	—	0.6	—	μs	$I_C = -10\text{ A}$, $I_{B1} = -I_{B2} = -20\text{ mA}$
Storage time	t_{stg}	—	3.5	—	μs	

Note: 1. Pulse Test.

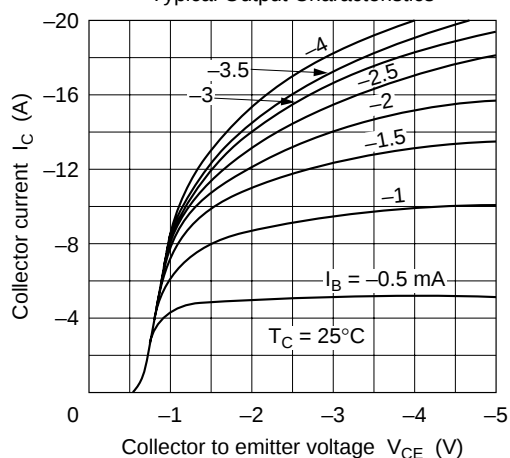
Maximum Collector Dissipation Curve



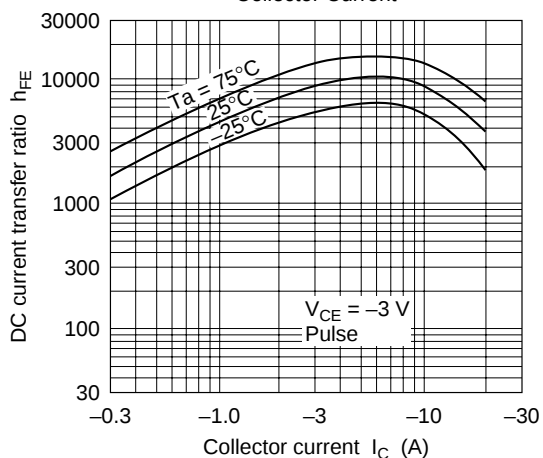
Area of Safe Operation

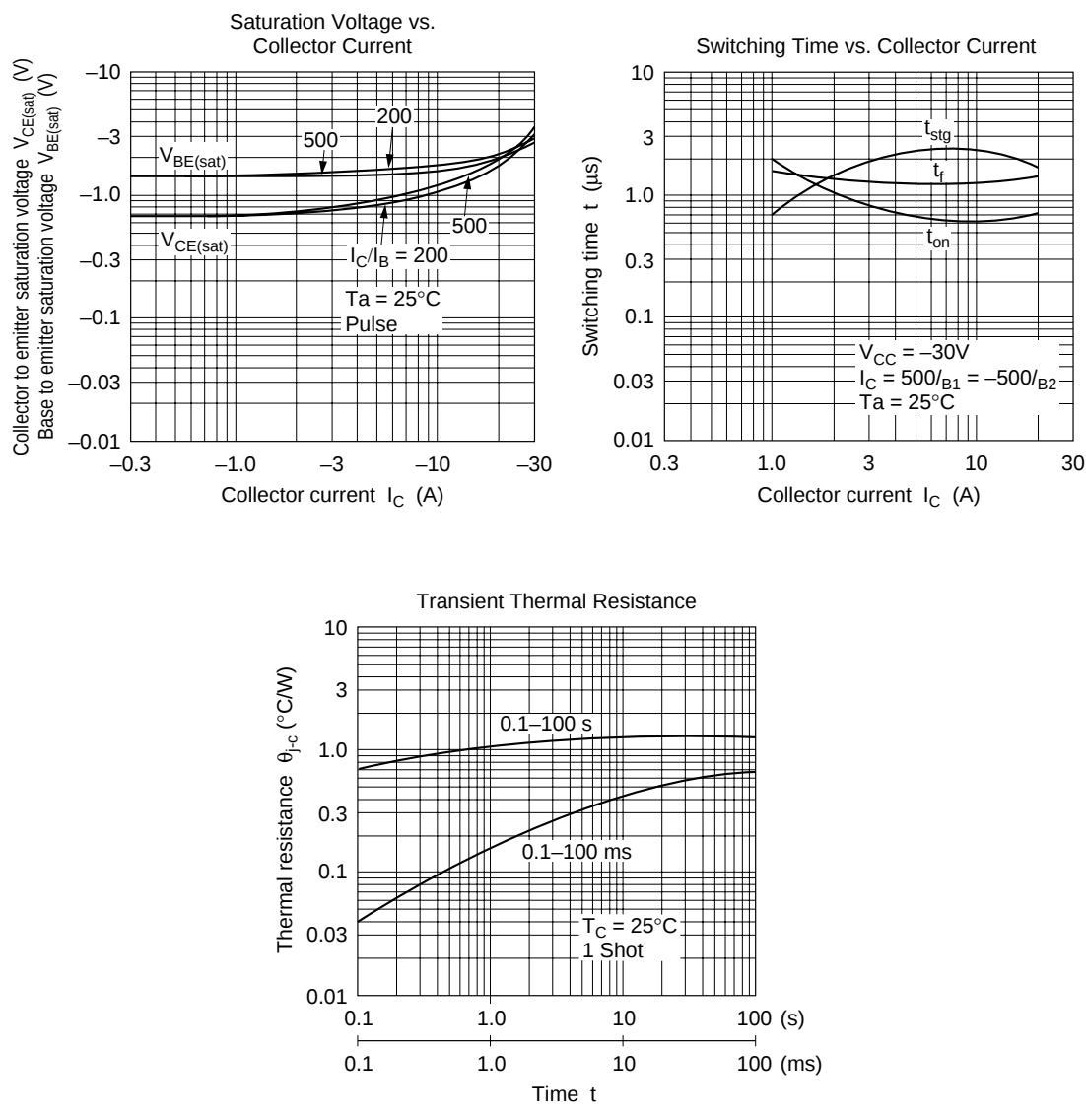


Typical Output Characteristics

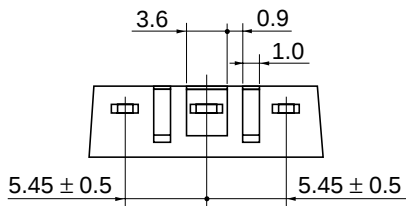
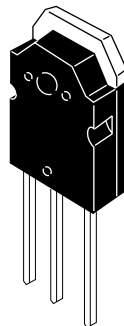
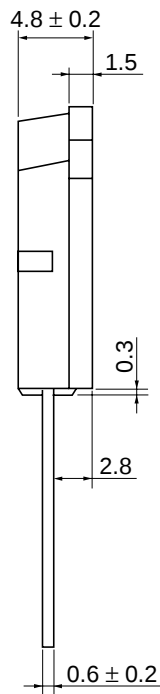
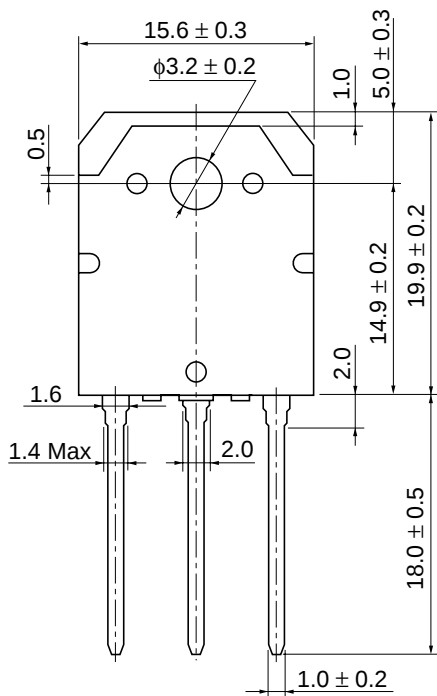


DC Current Transfer Ratio vs. Collector Current





Unit: mm



Hitachi Code	TO-3P
JEDEC	—
EIAJ	Conforms
Weight (reference value)	5.0 g

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